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Part 1 of 2
19 pages

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To: Examiner Phat X. Cao	From: Joanne Ryan
Fax: 703-872-9319	Pages: 28 including cover
Phone:	Date: 3/3/2004
Re: Serial No. 10/039,284	CC: [Click here and type name]

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Please see attached:

- (1) Explanatory Letter, 2 pp.
- (2) Transmittal of Information Disclosure Statement, Nov. 27, 2002, 2 pp.
- (3) PTO-1449, filed Nov. 27, 2002, 2 pp.
- (4) Copy of date-stamped receiptconfirmation postcard, 1 p.
- (5) Copies of 3 "other documents," 15 pp.
- (6) Transmittal of Information Disclosure Statement, January 30, 2004, 3 pp.
- (7) PTO-1449, filed January 30, 2004, 1 p.
- (8) Copy of date-stamped receiptconfirmation postcard, 1 p.

10/039,284

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Applicant: Richard A. Blanchard

Serial No.: 10/039,284

Filed: December 31, 2001

Title: High Voltage Power MOSFET Having a Voltage Sustaining Region . . .

Art Unit: 2814

Examiner: Phat X. Cao

Docket No.: GS 174

Via Facsimile: 703-872-9319

**Mail Stop Issue Fee
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450**

**EXPLANATORY LETTER ACCOMPANYING RE-FILED
INFORMATION DISCLOSURE STATEMENTS**

The above-referenced patent application received a Notice of Allowance dated November 10, 2003, and the Issue Fee was paid on February 10, 2004. The undersigned attorney has not received Examiner-initialed copies of the following Information Disclosure Statements filed in the application:

1. IDS filed November 27, 2002
2. IDS filed January 30, 2004

Pursuant to the request of the Examiner following a telephone conversation on February 10, 2004 between the Examiner and Joanne Ryan of the undersigned attorney's office, copies of each PTO-1449 are attached hereto. Copies of the date-stamped confirmation-receipt postcard for each IDS are attached as well. Also per Examiner Cao's instructions, copies of the US patents disclosed in the each IDS are not attached. Please find attached, however, copies of the three "other documents" disclosed in the IDS filed November 27, 2002.

As the application has been allowed and the Issue Fee has been paid, it is respectfully requested that the Examiner consider the art disclosed in each IDS listed above and forward an initialed copy of each PTO-1449 to the undersigned attorney at the Examiner's earliest opportunity.

Respectfully submitted,

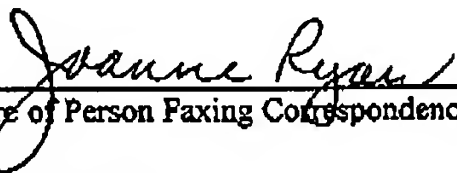


Keum J. Park

Registration No. 42,059

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I certify that this document and any document referenced herein has been transmitted via facsimile to the US Patent & Trademark Office at (703) 872-9319 on March 3, 2004.



Signature of Person Faxing Correspondence

Joanne Ryan

Typed or Printed Name of Person Faxing Correspondence

Supplement

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))			Docket No. GS 174
In Re Application Of: Richard A. Blanchard et al.			
Serial No. 10/039,284	Filing Date 12/31/01	Examiner Unassigned	Group Art Unit 2811
Title: HIGH VOLTAGE POWER MOSFET HAVING A VOLTAGE SUSTAINING REGION THAT INCLUDES DOPED COLUMNS FORMED BY TRENCH ETCHING USING AN ETCHANT GAS THAT IS ALSO A DOPING SOURCE			
<p style="text-align: center;">Address to: Assistant Commissioner for Patents Washington, D.C. 20231</p> <p style="text-align: center;">37 CFR 1.97(b)</p> <p>1. <input checked="" type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.</p> <p style="text-align: center;">37 CFR 1.97(c)</p> <p>2. <input type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:</p> <p style="margin-left: 40px;"><input type="checkbox"/> the statement specified in 37 CFR 1.97(e);</p> <p style="text-align: center; margin-left: 100px;">OR</p> <p style="margin-left: 40px;"><input type="checkbox"/> the fee set forth in 37 CFR 1.17(p).</p>			

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))			Docket No. GS 174
In Re Application: Richard A. Blanchard et al.			
Serial No. 18/039,284	Filing Date 12/31/01	Examiner Unassigned	Group Art Unit 2811
HIGH VOLTAGE POWER MOSFET HAVING A VOLTAGE SUSTAINING REGION THAT INCLUDES DOPED COLUMNS FORMED BY TRENCH ETCHING USING AN ETCHANT GAS THAT IS ALSO A DOPING SOURCE			
Payment of Fee (Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))			
<input type="checkbox"/> A check in the amount of _____ is attached. <input type="checkbox"/> The Assistant Commissioner is hereby authorized to charge and credit Deposit Account No. _____ as described below. A duplicate copy of this sheet is enclosed.			
<input type="checkbox"/> Charge the amount of _____ <input type="checkbox"/> Credit any overpayment. <input type="checkbox"/> Charge any additional fee required.			
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(Date) _____ Signature _____ Typed or Printed Name of Person Signing Certificate _____		11/27/02 Signature of Person Mailing Correspondence _____ Marjorie Seariad Typed or Printed Name of Person Mailing Certificate _____	
*This certificate may only be used if paying by deposit account.			
Karin L. Williams Signature		Dated: 11/27/02	
Karin L. Williams Reg. No. 36,721 Mayer Fortkort & Williams, PC 251 North Avenue West, 2nd Floor Westfield, NJ 07090 Tel.: 908-518-7780 Fax: 908-518-7795 CC:			

PDARPV02

Supplemental INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	ATTY DOCKET NO. CS 174		SERIAL NO. 10/039,284
	Richard A. Blanchard et al.		
	FILING 12/31/01	GROUP 2811	

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	1.	10/039,241		Blanchard			12/31/2001
	2.	10/038,845		Blanchard			12/31/2001
	3.	09/970,758		Blanchard et al.			10/4/2001
	4.	2001/0053568A1	12/20/2001	Deboy et al.	438	138	
	5.	2001/0036704A1	11/1/2001	Huetting et al.	438	270	
	6.	2001/0026977A1	10/4/2001	Hattori et al.	438	268	
	7.	5,216,275	6/1/93	Chen	257	493	
	8.	5,108,783	4/28/92	Tanigawa et al.	437	63	
	9.	4,893,160	1/9/90	Blanchard	357	23.4	
	10.	4,711,017	12/8/87	Lammert	437	20	

FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
	1.	Xing Bi Chen et al., "A Novel High-Voltage Sustaining Structure with Buried Oppositely Doped Regions," <i>IEEE Transactions on Electron Devices</i> , Vol. 47, No. 6, June 2000, pp. 1280-1285.
	2.	N. Cezac et al., "A New Generation of Power Unipolar Devices: the Concept of the Floating Islands MOS Transistor (FLIMOST)," Proceedings of the 12th International Symposium on Power Semiconductor Devices & ICs, Toulouse, France, May 22-25, 2000, pp. 69-72.

EXAMINER	DATE CONSIDERED
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<p><i>Supplemental</i></p> <p>INFORMATION DISCLOSURE CITATION</p> <p><i>(Use several sheets if necessary)</i></p>	<table border="1" style="width:100%; border-collapse: collapse;"> <tr> <td style="width:50%;">ATTY DOCKET NO. GS 174</td> <td style="width:50%;">SERIAL NO. 10/039,284</td> </tr> <tr> <td colspan="2">Richard A. Blanchard et al.</td> </tr> <tr> <td>FILING 12/31/01</td> <td>GROUP 2811</td> </tr> </table>	ATTY DOCKET NO. GS 174	SERIAL NO. 10/039,284	Richard A. Blanchard et al.		FILING 12/31/01	GROUP 2811
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Richard A. Blanchard et al.							
FILING 12/31/01	GROUP 2811						

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	11.	4,569,701	2/11/86	Oh	148	188
	12.	4,419,150	12/6/83	Soclof	148	187
	13.	4,140,558	2/20/79	Murphy et al.	148	175
	14.	10/039,068		Blanchard		12/31/01

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

3.	Ming-Kwang Lee et al., "On the Semi-Insulating Polycrystalline Silicon Resistor," <i>Solid State Electronics</i> , Vol. 27, No. 11, 1984, pp. 995-1001.

EXAMINER

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Docket GS 174 (2020/80)

Assistant Commissioner for Patents
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Serial No.: 10/039,284
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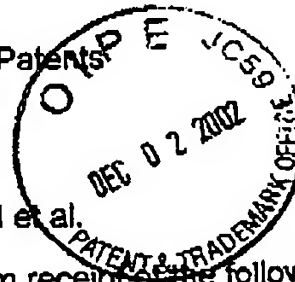
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